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**Jason P. Cain
Chi-Min Yuan**
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Contents

vii	<i>Authors</i>
ix	<i>Conference Committee</i>

SESSION 1	TRENDS IN DPTCO
10588 03	Efficient place and route enablement of 5-tracks standard-cells through EUV compatible N5 ruleset [10588-2]
10588 04	Patterning method impact on sub-36nm pitch interconnect variability [10588-3]
10588 05	Applying machine learning to pattern analysis for automated in-design layout optimization [10588-4]
SESSION 2	PATTERN CORRECTION METHODS: JOINT SESSION WITH CONFERENCES 10588 AND 10587
10588 06	Optimization of optical proximity correction to reduce mask write time using genetic algorithm [10588-5]
10588 07	Dependencies of bias tables to pattern density, critical dimension, global coordinates and pattern orientation for nanoimprint master manufacturing for the 200 mm wafer scale SmartNIL process [10588-6]
SESSION 3	DESIGN-TECHNOLOGY CO-OPTIMIZATION
10588 08	Pre-PDK block-level PPAC assessment of technology options for sub-7nm high-performance logic (Invited Paper) [10588-7]
10588 09	Track height reduction for standard-cell in below 5nm node: how low can you go? [10588-8]
10588 0A	A compact multi-bit flip-flop with smaller height implementation and metal-less intra-cell routing [10588-9]
10588 0B	DTCO exploration for efficient standard cell power rails [10588-10]
SESSION 4	LAYOUT OPTIMIZATION
10588 0C	Post-decomposition optimizations using pattern matching and rule-based clustering for multi-patterning technology [10588-11]

- 10588 OD **Pin routability and pin access analysis on standard cells for layout optimization** [10588-12]
- 10588 OE **Variability-aware double-patterning layout optimization for analog circuits** [10588-13]
- 10588 OF **Litho friendly via insertion with in-design auto-fix flow using machine learning** [10588-14]

SESSION 5 DESIGN INTERACTIONS: JOINT SESSION WITH CONFERENCES 10585 AND 10588

- 10588 OG **A model-based, Bayesian approach to the CF₄/Ar etch of SiO₂** [10588-15]

SESSION 6 PATTERN-BASED ANALYSIS

- 10588 OI **Hotspot detection based on surrounding optical feature** [10588-18]
- 10588 OJ **Range pattern matching with layer operations and continuous refinements** [10588-19]
- 10588 OK **Combinational optical rule check on hotspot detection**
[10588-20]
- 10588 OL **Pattern analysis and classification accelerates OPC tuning, monitoring, and optimization and mask inspection** [10588-21]

SESSION 7 ADVANCED PATTERNING

- 10588 ON **IMEC N7, N5 and beyond: DTCO, STCO and EUV insertion strategy to maintain affordable scaling trend (Invited Paper)** [10588-22]
- 10588 OO **Relaxing LER requirement in EUV lithography** [10588-23]
- 10588 OP **Comparison between multi-colored LEⁿ SADP/SAQP and selective-etching SADP/SAQP**
[10588-25]
- 10588 OQ **Integrated manufacturing flow for selective-etching SADP/SAQP** [10588-24]

POSTER SESSION

- 10588 OR **Timing optimization in SADP process through wire widening and double via insertion**
[10588-26]
- 10588 OS **Characterization of metal line-width variation in via first dual-damascene approach and its modeling using machine learning artificial neural network algorithms** [10588-27]
- 10588 OT **Cross-MEEF assisted SRAF print avoidance approach** [10588-28]
- 10588 OU **A weak pattern random creation and scoring method for lithography process tuning**
[10588-29]

10588 0V	Pattern-based IP block detection, verification, and variability analysis [10588-30]
10588 0W	A smart way to identify and extract repeated patterns of a layout [10588-31]
10588 0X	Using pattern based layout comparison for a quick analysis of design changes [10588-32]
10588 0Y	An efficient way of layout processing based on calibre DRC and pattern matching for defects inspection application [10588-33]
10588 0Z	Leveraging pattern matching to solve SRAM verification challenges at advanced nodes [10588-34]
10588 10	A portable pattern-based design technology co-optimization flow to reduce optical proximity correction run-time [10588-35]
10588 11	Hybrid hotspot library building based on optical and geometry analysis at early stage for new node development [10588-36]

Authors

Numbers in the index correspond to the last two digits of the six-digit citation identifier (CID) article numbering system used in Proceedings of SPIE. The first four digits reflect the volume number. Base 36 numbering is employed for the last two digits and indicates the order of articles within the volume. Numbers start with 00, 01, 02, 03, 04, 05, 06, 07, 08, 09, 0A, 0B...0Z, followed by 10-1Z, 20-2Z, etc.

Abe, Yayori, 0I	Gillijns, Werner, 0N
Ahmad Ibrahim, Muhamad Asraf Bin, 0V	Gu, Tingting, 0W
Ali, Rehab Kotb, 0P, 0Q	Gupta, Puneet, 0O
Asthana, Abhishek, 06	Han, G., 08
Baert, R., 03	Helpert, Sofia, 0G
Bakshi, Janam, 0F	Hu, Xinyi, 0U, 0W, 0X, 0Y, 0Z
Batarseh, Fadi, 0F	Huang, Elven, 0Z
Baum, Z., 08	Huang, Lucas, 0X, 0Z
Berekovic, M., 03	Hurat, Philippe, 0L, 0V, 10
Blanco, Victor, 0N	Hyun, Daijoon, 0R
Bonnecaze, Roger, 0G	Ismail, Mohamed, 0F
Boudaa, F., 07	Jung, Jinwook, 0A, 0R
Brown, William, 0T	Kabeel, Aliaa, 0U
Cain, Jason P., 05, 0F	Kajiwara, Masanari, 0I
Cantù, Pietro, 0S	Kamal Baharin, Ezni Aznida Binti, 0V
Cao, Liang, 06	Kan, Huan, 0X, 0Z
Catarisano, Chiara, 0S	Kim, Ryoung-Han, 03, 09, 0N
Chae, Jung Kyu, 09	Kotani, Toshiya, 0I
Chanemougame, D., 08	Kwan, Joe, 0U
Chartoire, J., 07	Lai, Ya-Chieh, 05, 0D, 0L, 0V, 10
Chava, Bharani, 0B	Lee, Jae Uk, 0N
Chen, Han, 0W	Lee, Robben, 0Y
Chen, James C.-H., 04	Lee, Tyzy, 0Y
Chen, Jian, 0D	Lee, Zhao Chuan, 0E, 0J
Chen, Kao-Tun, 10	Li, Helen, 0Y
Chen, Yi-Chieh, 10	Li, Shuai, 0D
Chen, Ying, 11	Li, Tsung-Han, 10
Cheng, Jing, 06	Li, Yongfu, 0E, 0J
Chopra, Meghali, 0G	LiCausi, Nicholas V., 04
Chu, Zhihao, 0W	Liebmman, L., 08
Corneo, Nicoletta, 0S	Lin, Eason, 0D
Debacker, Peter, 03, 09, 0B, 0N	Lin, Hung-Yu, 10
Delachat, F., 07	Lippincott, George, 0T
Deng, Guogui, 0U	Litterio, Emma, 0S
Dick, Gregory J., 06	Liu, Hermes, 0Y
Du, Chunshan, 0U, 0W, 0X, 0Y, 0Z	Liu, Zhengfang, 0U, 0W, 0X, 0Y, 0Z
Dundulachi, Alessandro, 0S	Liubich, Vlad, 0T
ElManhawly, Wael, 0U	Luo, Yandong, 0O
Elsemary, Ahmed Mounir, 0F	Lupa, Paul, 0L
Facchini, M., 08	Ma, Yuansheng, 0K
Fakhry, Moutaz, 05, 0F	Madhavan, Sriram, 0C
Fatehy, Ahmed Hamed, 0P, 0Q	Madkour, Kareem, 0U
Gai, Tianyang, 11	Malik, Arindam, 0N
Gao, Gensheng, 0U	Mantovani, Valeria, 0S
Gao, Shaowen, 0K	Mattii, Luca, 03, 09, 0B
Gennari, Frank, 05	May, M., 07
Gerosis, V., 03, 08, 09	McIntyre, Greg, 0N

Milojevic, D., 03	Xue, Teddy, 0Y
Mocuta, A., 09	Yang, Legender, 0X, 0Z
Mohyeldin, Ahmed, 0F	Ye, Tianchun, 11
Muhsain, Mohamad Fahmi Bin, 0V	Yin, Lianghong, 0K
Muirhead, Jonathan, 0Z	Yu, Shirui, 0U
Nakajima, Fumiharu, 0I	Zhang, Chenming, 0W
Nakamoto, N., 08	Zhang, Hongxin, 0K
Nojima, Shigeki, 0I	Zhang, Meili, 0U
Northrop, G., 08	Zhang, Recoo, 0Z
Ong, Jonathan Yoong Seang, 0E, 0J	Zhang, Zizhuo, 0G
Ou, Odie, 0D	Zhu, ChengYu, 0D
Patelmo, Matteo, 0S	Zhu, Jun, 0W
Pathak, Piyush, 05	Zhu, Xilan, 0G
Perez, Valerio, 0E, 0J	Zhu, Yu, 0Z
Perraud, L., 07	Zou, Elaine, 0X, 0Z
Power, David N., 06	
Qu, Shengrui, 0D	
Quemere, P., 07	
Raghavan, Praveen, 03, 09, 0N	
Riviere-Cazaux, L., 08	
Ronse, Kurt, 0N	
Ryan, E. Todd, 04	
Ryckaert, Julien, 03, 09, 0B, 0N	
Schroeder, Uwe Paul, 0F	
Seo, Jaewoo, 0A	
Shah, Nishant, 0F	
Shang, Shumay, 0K	
Sherazi, Syed Muhammad Yasser, 03, 09, 0B, 0N	
Shin, Youngsoo, 0A, 0R	
Smith, R. S., 04	
Song, Youngsoo, 0R	
Spessot, Alessio, 09, 0B	
Su, Xiaojing, 11	
Su, Yajuan, 11	
Sun, K., 08	
Sun, Yuyang, 0K	
Sweis, Jason, 05, 0L, 0V	
Tan, Ling Ee, 0N	
Teyssedre, H., 07	
Tripathi, Vikas, 0E, 0J	
Triulzi, Benedetta, 0S	
Tseng, I-Lun, 0E, 0J	
Verkest, Diederik, 03, 09, 0B, 0N	
Verma, Rahul, 0G	
Wan, Qijian, 0U, 0W, 0X, 0Y, 0Z	
Wang, Jun, 0D	
Wang, Lynn T.-N., 0C	
Wang, Mudan, 0U	
Wang, Ruoping, 0L	
Watanabe, Yuki, 0I	
Wei, Alexander, 0K	
Wei, Fang, 0W	
Wei, Yayi, 11	
Word, James, 0P, 0Q	
Wu, Chun-Sheng, 10	
Wu, Hall, 0Y	
Wu, Rui, 0K, 0T	
Xu, Wei, 0D	

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- 1 Trends in DPTCO
Jason P. Cain, Advanced Micro Devices, Inc. (United States)
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- 2 Pattern Correction Methods: Joint Session with Conferences 10588 and 10587
Neal V. Lafferty, Mentor, a Siemens Business (United States)
Carlos Fonseca, Tokyo Electron America, Inc. (United States)
- 3 Design-Technology Co-optimization
Ru-Gun Liu, Taiwan Semiconductor Manufacturing Company Ltd. (Taiwan)
Vivek K. Singh, Intel Corporation (United States)
- 4 Layout Optimization
Luigi Capodieci, KnotPrime, Inc. (United States)
Michael L. Rieger, Consultant (United States)
- 5 Design Interactions: Joint Session with Conferences 10585 and 10588
John C. Robinson, KLA-Tencor Corporation (United States)
Ryoung-Han Kim, imec (Belgium)
- 6 Pattern-based Analysis
Lifu Chang, Qualcomm Inc. (United States)
Lars W. Liebmann, GLOBALFOUNDRIES Inc. (United States)
- 7 Advanced Patterning
Shigeki Nojima, Toshiba Corporation (Japan)
Lynn T.-N. Wang, GLOBALFOUNDRIES Inc. (United States)